



FRED

V_{RRM}	=	200 V
I_{FAV}	=	60 A
t_{rr}	=	20 ns

Fast Recovery Epitaxial Diode Single Diode

Part number

DSEI60-02A



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			200	V	
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			200	V	
I_R	reverse current, drain current	$V_R = 200 V$	$T_{VJ} = 25^{\circ}C$		50	μA	
		$V_R = 160 V$	$T_{VJ} = 125^{\circ}C$		11	mA	
V_F	forward voltage drop	$I_F = 60 A$	$T_{VJ} = 25^{\circ}C$		1.10	V	
		$I_F = 120 A$			1.31	V	
		$I_F = 60 A$	$T_{VJ} = 150^{\circ}C$		0.95	V	
		$I_F = 120 A$			1.22	V	
I_{FAV}	average forward current	$T_C = 115^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}C$		60	A	
V_{FO}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0.69	V	
r_F	slope resistance				4.3	m Ω	
R_{thJC}	thermal resistance junction to case				0.5	K/W	
R_{thCH}	thermal resistance case to heatsink			0.25		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		250	W	
I_{FSM}	max. forward surge current	$t = 10 ms; (50 Hz), sine; V_R = 0 V$	$T_{VJ} = 45^{\circ}C$		600	A	
C_J	junction capacitance	$V_R = 200 V$ $f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		170	pF	
I_{RM}	max. reverse recovery current	} $I_F = 70 A; V_R = 100 V$ $-di_F/dt = 400 A/\mu s$	$T_{VJ} = 25^{\circ}C$		6.5	A	
			$T_{VJ} = 100^{\circ}C$		11	A	
t_{rr}	reverse recovery time		$T_{VJ} = 25^{\circ}C$		20	ns	
			$T_{VJ} = 100^{\circ}C$		50	ns	



Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			70	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI60-02A	DSEI60-02A	Tube	30	471879

Equivalent Circuits for Simulation

** on die level*

$T_{VJ} = 150^{\circ}C$



Fast Diode

$V_{0\ max}$	threshold voltage	0.69	V
$R_{0\ max}$	slope resistance *	1.8	mΩ



Outlines TO-247



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.430 BSC		10.92 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
$\varnothing P$	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
$\varnothing P1$	-	0.29	-	7.39



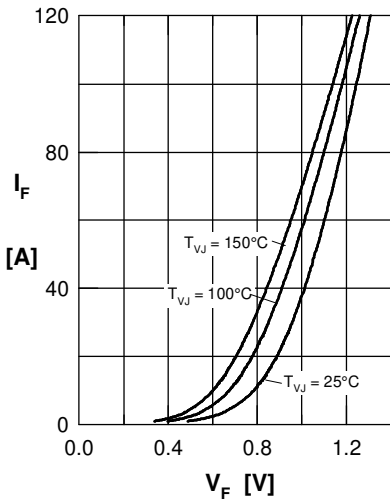
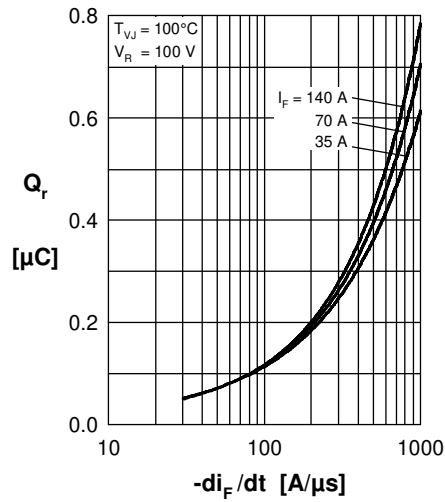
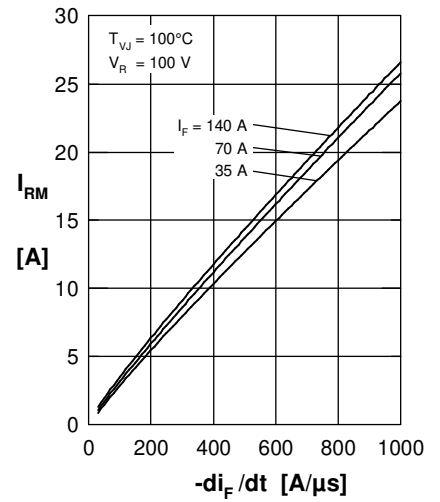
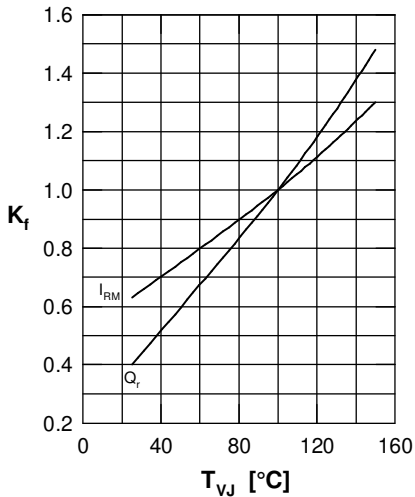
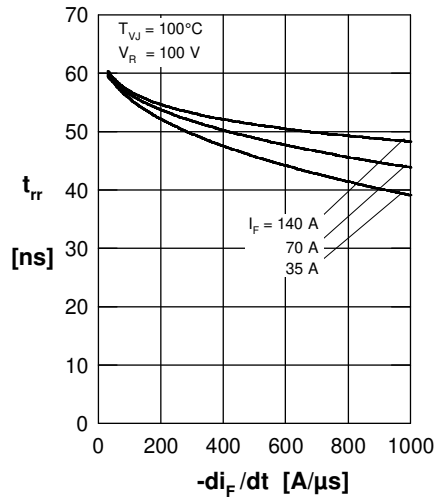
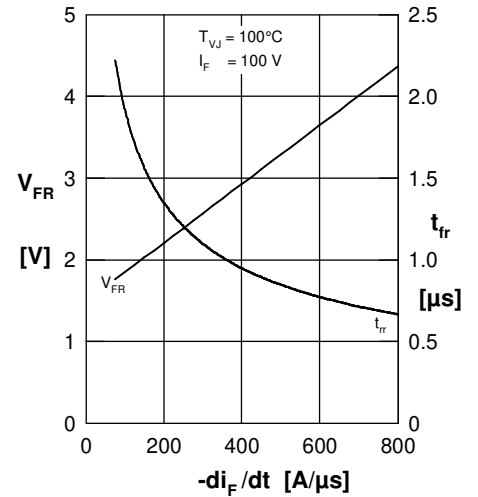
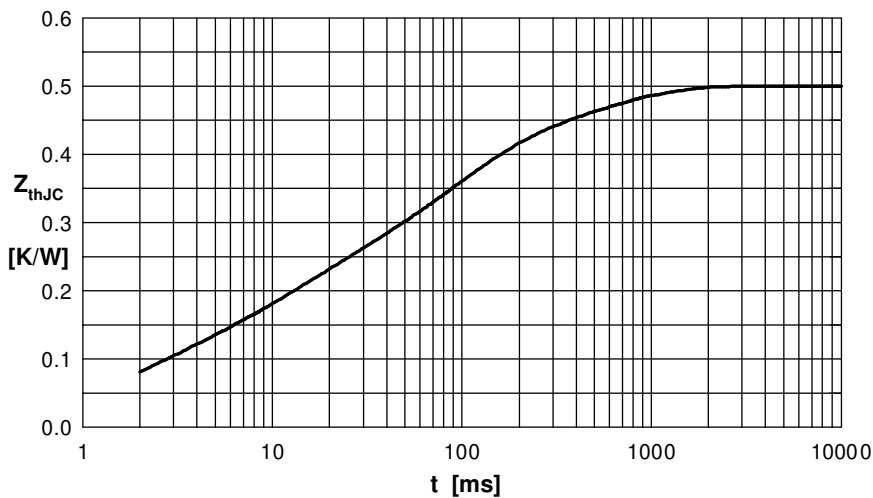
Fast Diode

 Fig. 1 Forward current I_F versus max. forward voltage drop V_F

 Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

 Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

 Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

 Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

 Fig. 6 Typ. peak forward voltage V_{FR} and t_{rr} versus di_F/dt


Fig. 7 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.080	0.0018
2	0.120	0.0100
3	0.100	0.5000
4	0.200	0.0800